

Features

- 20V/3.5A,
 $R_{DS(ON)} = 43m\Omega(Typ.)@V_{GS}=4.5V$
 $R_{DS(ON)} = 55m\Omega(Typ.)@V_{GS}=2.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

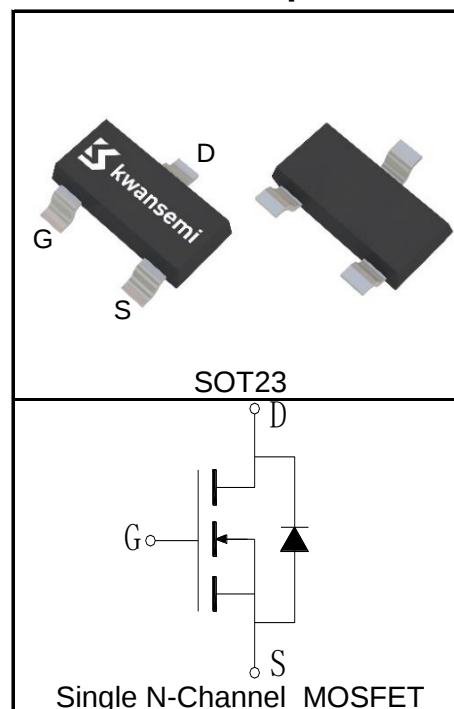
Applications

- Load Switch



Halogen-Free

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	
T_{Jmax}	Maximum Junction Temperature	150	$^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$ 1.1	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ 14	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=4.5V$)	$T_A=25^\circ\text{C}$ 3.5	A
		$T_A=70^\circ\text{C}$ 2.8	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 1	W
		$T_A=70^\circ\text{C}$ 0.64	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	80	$^\circ\text{C/W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	125	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	2	mJ

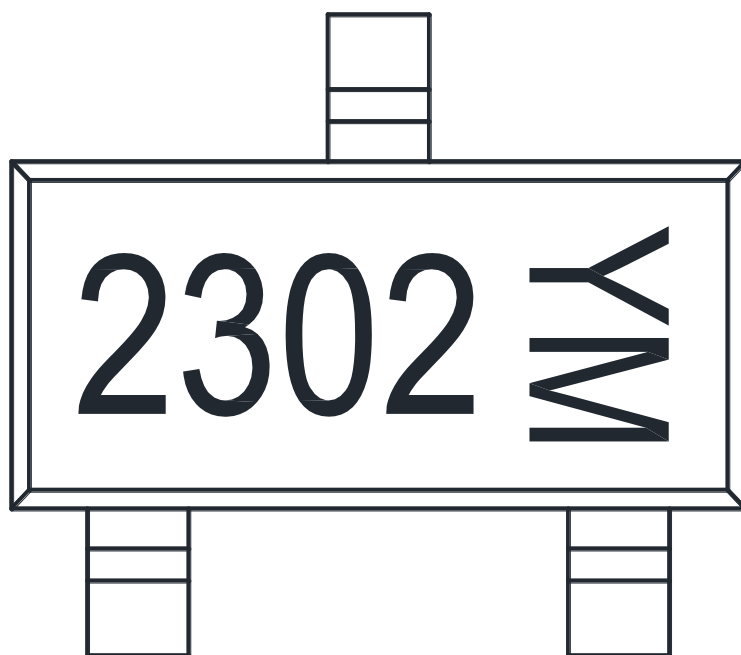
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Rating			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.4	0.65	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =2A		43	55	mΩ
		V _{GS} =2.5V, I _{DS} =1.5A		55	70	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =2A, V _{GS} =0V		0.86	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =2A, dI _{SD} /dt=100A/μs		13		ns
Q _{rr}	Reverse Recovery Charge			7		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		3.5		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz		125		pF
C _{oss}	Output Capacitance			20		
C _{rss}	Reverse Transfer Capacitance			17		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, I _{DS} =2A, V _{GEN} =4.5V, R _G =6Ω		11		ns
t _r	Turn-on Rise Time			46		
t _{d(OFF)}	Turn-off Delay Time			18		
t _f	Turn-off Fall Time			11		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =2A		2		nC
Q _{gs}	Gate-Source Charge			0.2		
Q _{gd}	Gate-Drain Charge			0.6		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = 3A$, $L = 0.5\text{mH}$, $V_{DD}=12V$, $R_G = 25\Omega$, $V_{GS}=4.5V$. Part not recommended for use above this value.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

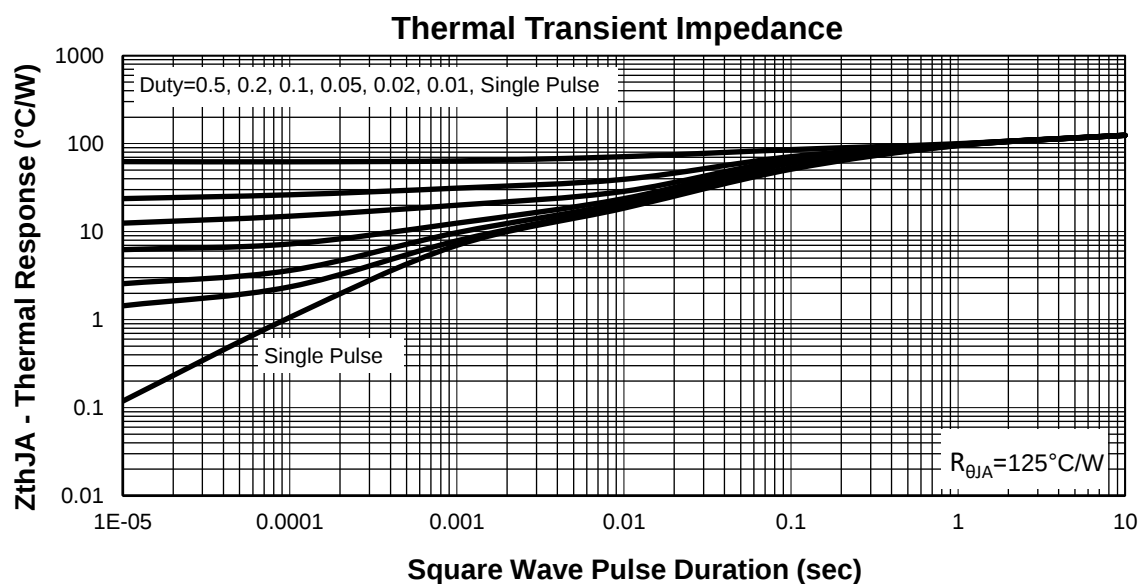
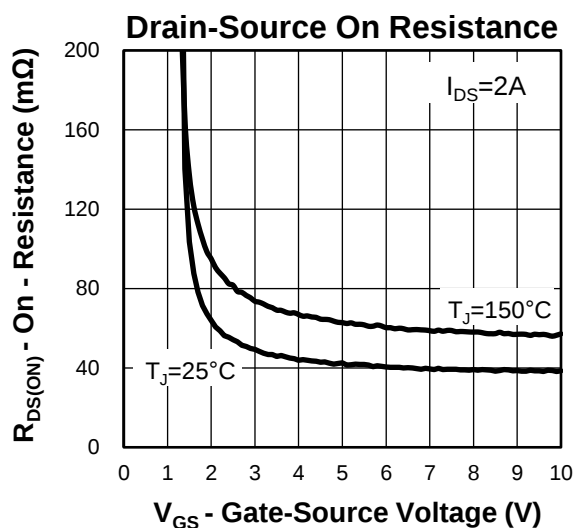
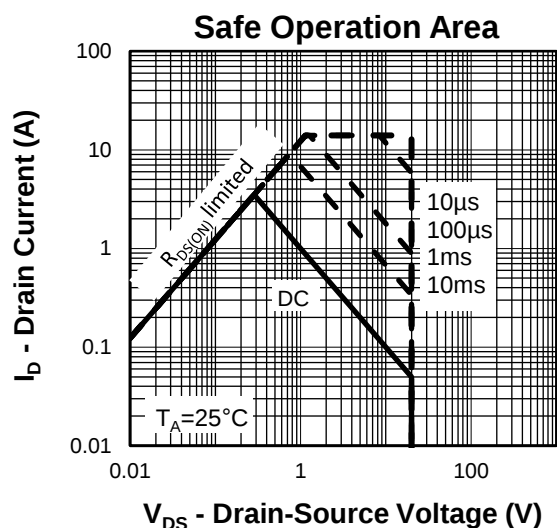
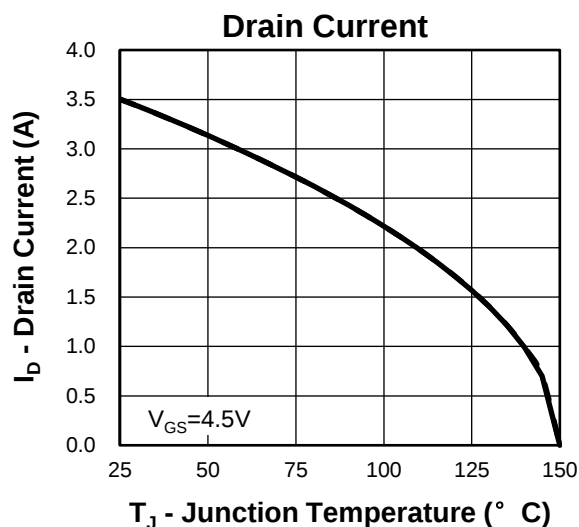
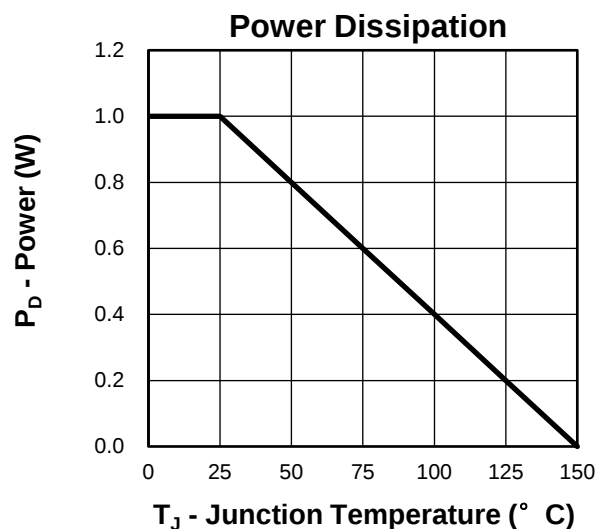
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS2302AB	SOT23	Tape&Reel	3000	7"	8mm



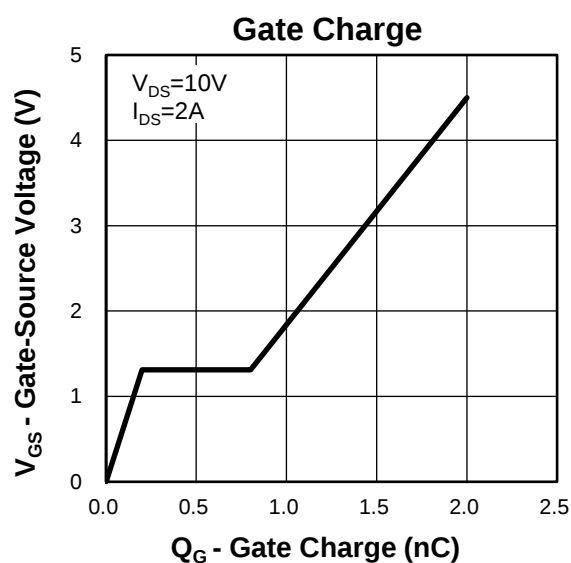
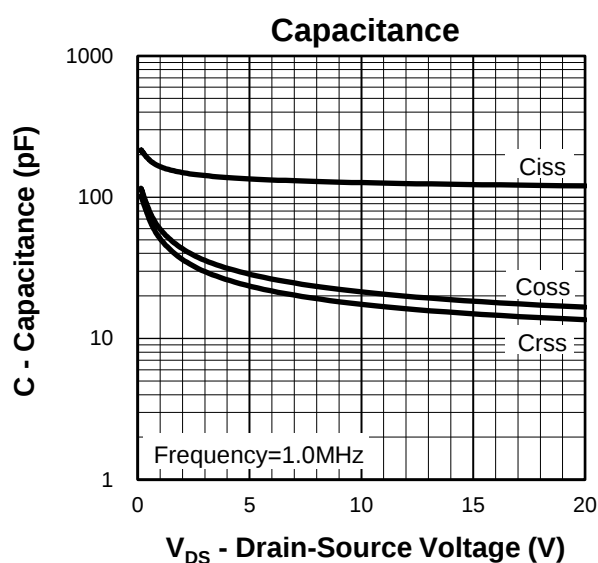
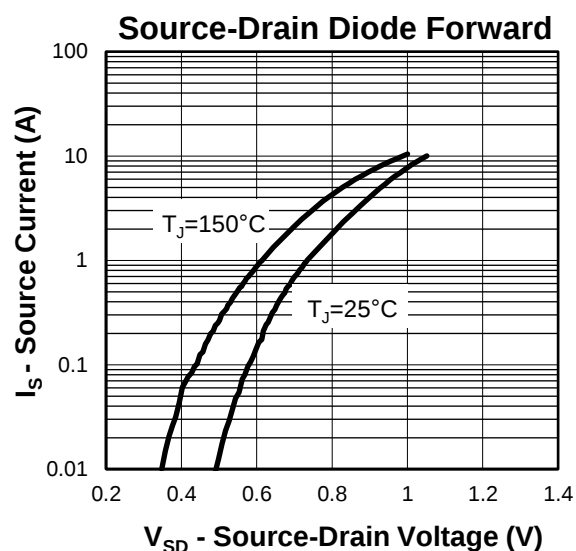
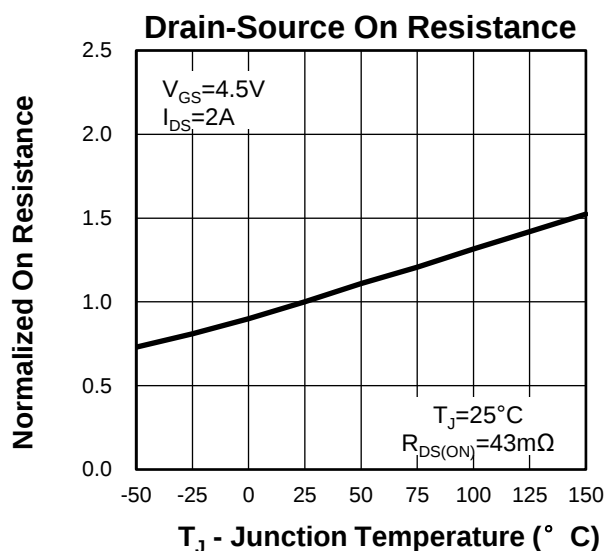
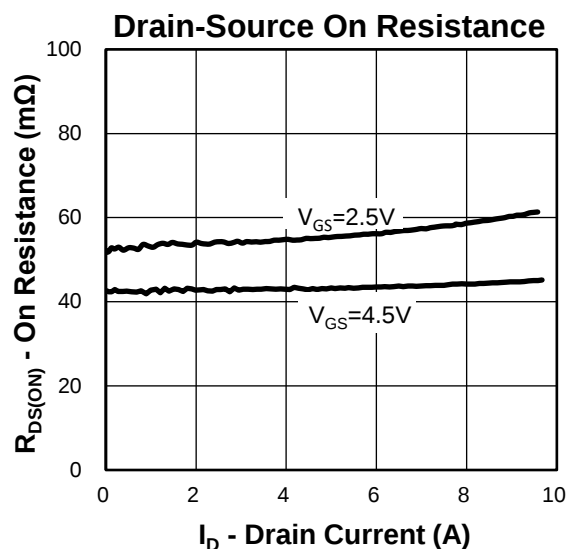
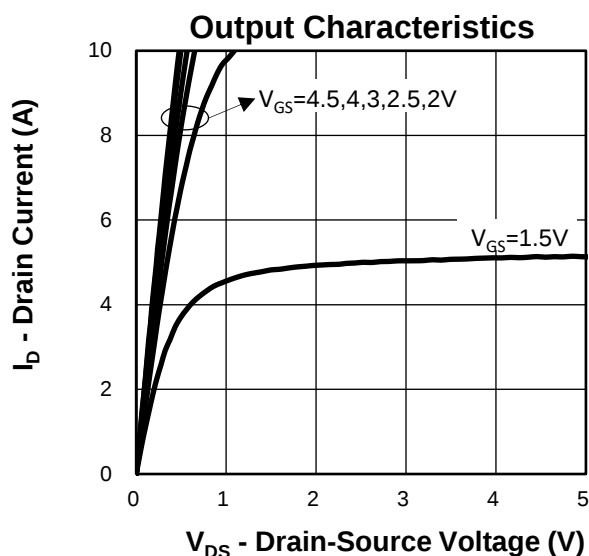
Y =Year,2017-A,2018-B,etc.

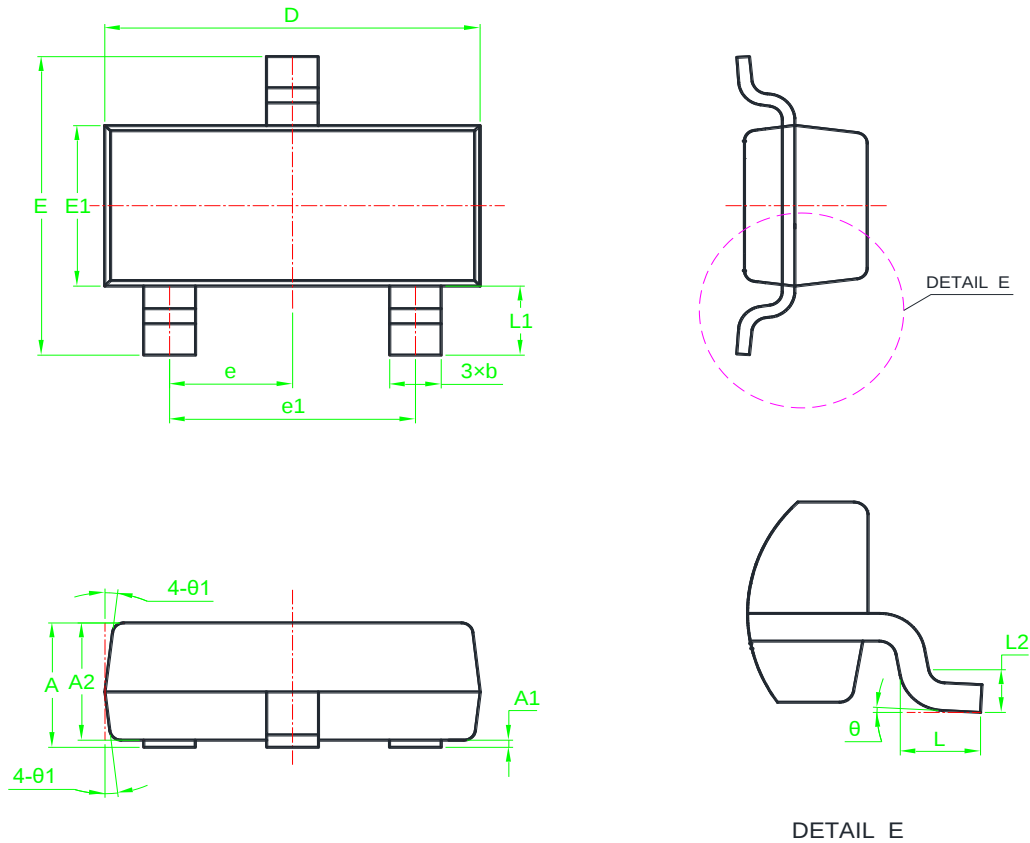
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Typical Characteristics



Typical Characteristics

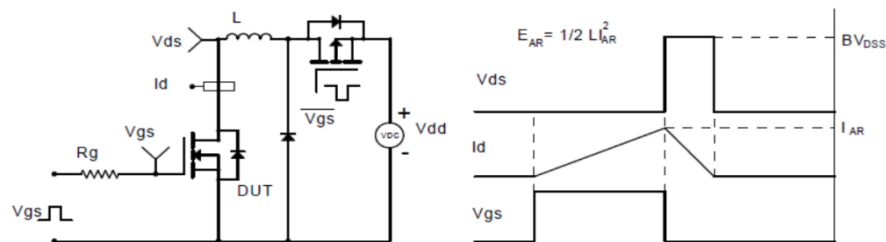


Package Information
SOT23


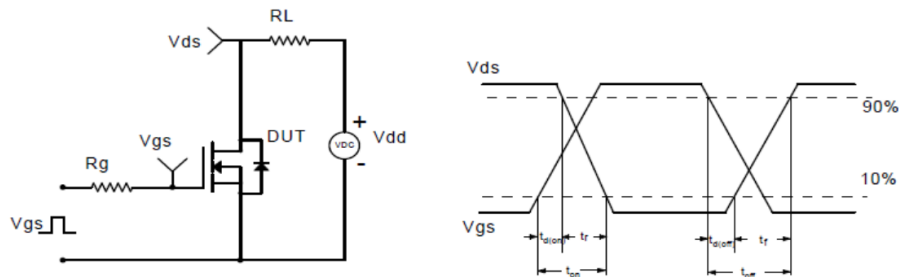
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	*	1.12	0.035	*	0.044	e	0.95BSC			0.037BSC		
A1	0.01	*	0.10	0.000	*	0.004	e1	1.90BSC			0.075BSC		
A2	0.80	0.90	1.02	0.031	0.035	0.040	L	0.30	0.40	0.50	0.012	0.016	0.020
b	0.30	0.40	0.50	0.012	0.016	0.020	L1	0.54REF			0.021REF		
D	2.80	2.90	3.00	0.110	0.114	0.118	L2	0.254BSC			0.010BSC		
E	2.25	2.40	2.55	0.089	0.094	0.100	θ	0°	*	8°	0°	*	8°
E1	1.20	1.30	1.40	0.047	0.051	0.055	θ 1	0°	*	10°	0°	*	10°

Note: Dimensions do not inclusive burrs and mold flash.

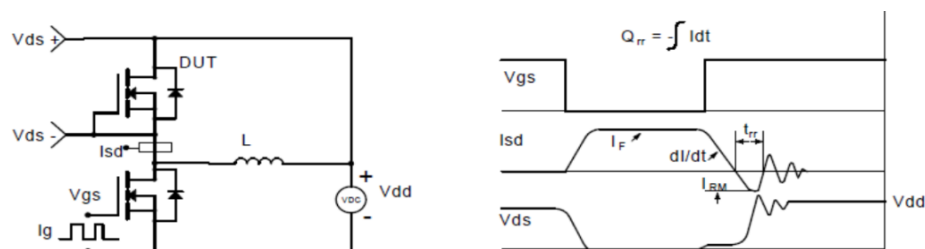
Avalanche Test Circuit and Waveforms



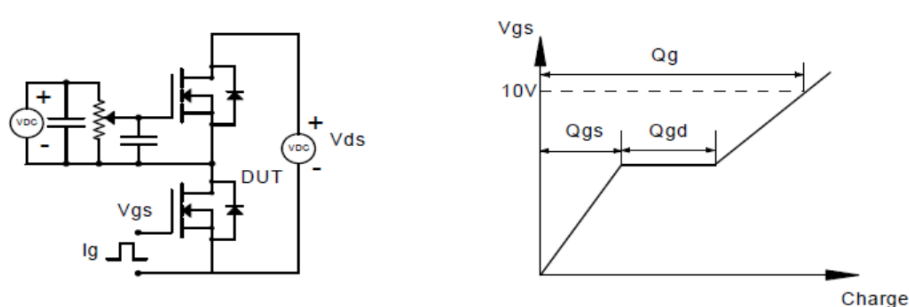
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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